Stephen J Pearton

List of Publications by Year in Descending Order

2,108 papers	59,415 citations	98 h-index	180 g-index
2,179 ext. papers	63,400 ext. citations	3 avg, IF	7.53 L-index

#	Paper	IF	Citations
2108	Variable temperature probing of minority carrier transport and optical properties in p-Ga2O3. *APL Materials*, **2022**, 10, 031106	5.6	1
2107	Deep level defect states in □ and e-Ga2O3 crystals and films: Impact on device performance. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2022**, 40, 020804	2.7	2
2106	Exfoliated and bulk □gallium oxide electronic and photonic devices **2022**, 1, 100001		0
2105	Thermo-mechanical aspects of gamma irradiation effects on GaN HEMTs. *Applied Physics Letters*, **2022**, 120, 124101	3.3	1
2104	Betavoltaic cell based on Ni/□Ga2O3 and 63Ni source. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2022**, 40, 010401	2.7	0
2103	Communication□Electron-Beam Stimulated Release of Dislocations from Pinning Sites in GaN. *ECS Journal of Solid State Science and Technology*, **2022**, 11, 015003	1.9	
2102	Impurity-hydrogen complexes in □Ga2O3: Hydrogenation of shallow donors vs deep acceptors. *Journal of Applied Physics*, **2022**, 131, 035706	2.4	0
2101	Digital biosensor for human cerebrospinal fluid detection with single-use sensing strips. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2022**, 40, 023202	1.2	0
2100	Rapid SARS-CoV-2 diagnosis using disposable strips and a metal-oxide-semiconductor field-effect transistor platform. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2022**, 40, 023204	1.2	1
2099	H trapping at the metastable cation vacancy in □Ga2O3 and □Al2O3. *Applied Physics Letters*, **2022**, 120, 192101	3.3	0
2098	Electrical properties of □Ga2O3 films grown by halide vapor phase epitaxy on sapphire with □Cr2O3 buffers. *Journal of Applied Physics*, **2022**, 131, 215701	2.4	
2097	Structural and electrical properties of thick □Ga2O3 grown on GaN/sapphire templates. *APL Materials*, **2022**, 10, 061102	5.6	
2096	Growth and characterization of (Sc2O3)x(Ga2O3)1□ by molecular beam epitaxy. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2022**, 40, 043403	2.7	
2095	Thermal effects in Ga2O3 rectifiers and MOSFETs borrowing from GaN **2022**, 441-467		
2094	Neuromorphic Devices: Artificial Neuron and Synapse Devices Based on 2D Materials (Small 20/2021). *Small*, **2021**, 17, 2170092	10.8	
2093	Electrical properties and deep trap spectra in Ga2O3 films grown by halide vapor phase epitaxy on p-type diamond substrates. *Journal of Applied Physics*, **2021**, 129, 185701	2.4	3
2092	Crystal orientation dependence of deep level spectra in proton irradiated bulk □Ga2O3. *Journal of Applied Physics*, **2021**, 130, 035701	2.4	3

2091	Review Opportunities in Single Event Effects in Radiation-Exposed SiC and GaN Power Electronics. *ECS Journal of Solid State Science and Technology*, **2021**, 10, 075004	1.9	4
2090	Post dry etching treatment of nanopillar GaN/InGaN multi-quantum-wells. *Journal of Alloys and Compounds*, **2021**, 868, 159211	5.6	0
2089	OH-Si complex in hydrogenated n-type Ga2O3:Si. *Applied Physics Letters*, **2021**, 119, 062109	3.3	5
2088	Magneto-optical properties of Cr3+ in Ga2O3. *Applied Physics Letters*, **2021**, 119, 052101	3.3	4
2087	Temperature dependent performance of ITO Schottky contacts on Ga2O3. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2021**, 39, 053405	2.7	4
2086	Design of Ga2O3 modulation doped field effect transistors. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2021**, 39, 023412	2.7	4
2085	Parasitic p n junctions formed at V-pit defects in p-GaN. *Journal of Applied Physics*, **2021**, 129, 155702	2.4	1
2084	Artificial Neuron and Synapse Devices Based on 2D Materials. *Small*, **2021**, 17, e2100640	10.8	10
2083	Vertical Ga2O3 Schottky rectifiers with 750 V reverse breakdown voltage at 600 K. *Journal Physics D: Applied Physics*, **2021**, 54, 305103	2.9	3
2082	Fast SARS-CoV-2 virus detection using disposable cartridge strips and a semiconductor-based biosensor platform. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2021**, 39, 033202	1.2	4
2081	Review Radiation Damage in Wide and Ultra-Wide Bandgap Semiconductors. *ECS Journal of Solid State Science and Technology*, **2021**, 10, 055008	1.9	13
2080	Experimental estimation of electron hole pair creation energy in Ga2O3. *Applied Physics Letters*, **2021**, 118, 202106	3.3	4
2079	Electron beam probing of non-equilibrium carrier dynamics in 18 MeV alpha particle- and 10 MeV proton-irradiated Si-doped Ga2O3 Schottky rectifiers. *Applied Physics Letters*, **2021**, 118, 202105	3.3	3
2078	Thermal Stability of Transparent ITO/n-Ga2O3/n+-Ga2O3/ITO Rectifiers. *ECS Journal of Solid State Science and Technology*, **2021**, 10, 115005	1.9	
2077	Al Composition Dependence of Band Offsets for SiO2 on (AlxGa1)2O3. *ECS Journal of Solid State Science and Technology*, **2021**, 10, 113007	1.9	1
2076	1 GeV proton damage in Ga2O3. *Journal of Applied Physics*, **2021**, 130, 185701	2.4	1
2075	Temperature dependence of cathodoluminescence emission in irradiated Si-doped Ga2O3. *AIP Advances*, **2021**, 11, 125014	1.5	1
2074	On the nature of photosensitivity gain in Ga2O3 Schottky diode detectors: Effects of hole trapping by deep acceptors. *Journal of Alloys and Compounds*, **2021**, 879, 160394	5.6	5

2073	Dislocations introduced in n-GaN at room temperature cause conductivity inversion. *Journal of Alloys and Compounds*, **2021**, 877, 160281	5.6	1
2072	Nitrogen ion-implanted resistive regions for edge termination of vertical Ga2O3 rectifiers. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2021**, 39, 063405	2.7	3
2071	Diffusion of dopants and impurities in Ga2O3. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2021**, 39, 060801	2.7	5
2070	Assessment of the (010) Ga2O3 surface and substrate specification. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2021**, 39, 013408	2.7	2
2069	Effect of probe geometry during measurement of >100 A Ga2O3 vertical rectifiers. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2021**, 39, 013406	2.7	8
2068	Review Opportunities for Rapid, Sensitive Detection of Troponin and Cerebral Spinal Fluid Using Semiconductor Sensors. *Journal of the Electrochemical Society*, **2020**, 167, 037507	3.8	3
2067	Structural transition and recovery of Ge implanted Ga2O3. *Applied Physics Letters*, **2020**, 117, 152101	3.3	13
2066	Effects of 5 MeV electron irradiation on deep traps and electroluminescence from near-UV InGaN/GaN single quantum well light-emitting diodes with and without InAlN superlattice underlayer. *Journal Physics D: Applied Physics*, **2020**, 53, 445111	2.9	2
2065	A Two-Electrode, Double-Pulsed Sensor Readout Circuit for Cardiac Troponin I Measurement. *IEEE Transactions on Biomedical Circuits and Systems*, **2020**, 14, 1362-1370	4.6	2
2064	Impact of electron injection on carrier transport and recombination in unintentionally doped GaN. *Journal of Applied Physics*, **2020**, 128, 085702	2.4	4
2063	Rapid Electrochemical Detection for SARS-CoV-2 and Cardiac Troponin I Using Low-Cost, Disposable and Modular Biosensor System **2020**,		4
2062	Band offset determination for amorphous Al2O3 deposited on bulk AlN and atomic-layer epitaxial AlN on sapphire. *Applied Physics Letters*, **2020**, 117, 182103	3.3	2
2061	Photosensitivity of Ga2O3 Schottky diodes: Effects of deep acceptor traps present before and after neutron irradiation. *APL Materials*, **2020**, 8, 111105	5.6	10
2060	Anisotropy of hydrogen plasma effects in bulk n-type Ga2O3. *Journal of Applied Physics*, **2020**, 127, 175702	2.4	11
2059	Effect of Electron Injection on Minority Carrier Transport in 10 MeV Proton Irradiated Ga2O3 Schottky Rectifiers. *ECS Journal of Solid State Science and Technology*, **2020**, 9, 045018	1.9	5
2058	Alpha Particle Irradiation of High Aluminum Content AlGan Polarization Doped Field Effect Transistors. *ECS Journal of Solid State Science and Technology*, **2020**, 9, 035008	1.9	2
2057	AlGaN/GaN heterostructure based Pt nanonetwork Schottky diode with water-blocking layer. *Sensors and Actuators B: Chemical*, **2020**, 317, 128234	8.3	3
2056	In Situ Transmission Electron Microscopy Observations of Forward Bias Degradation of Vertical Geometry Ga2O3 Rectifiers. *ECS Journal of Solid State Science and Technology*, **2020**, 9, 055008	1.9	1

2055	Annealing Effects on the Band Alignment of ALD SiO2 on (InxGa1□x)2O3 for x = 0.25□0.74. *ECS Journal of Solid State Science and Technology*, **2020**, 9, 045001	1.9	
2054	Asymmetrical Contact Geometry to Reduce Forward-Bias Degradation in □Ga2O3 Rectifiers. *ECS Journal of Solid State Science and Technology*, **2020**, 9, 035007	1.9	3
2053	Changes in band alignment during annealing at 600 °C of ALD Al2O3 on (InxGa1 □x)2O3 for x = 0.25□0.74. *Journal of Applied Physics*, **2020**, 127, 105701	2.4	2
2052	Deep traps in InGaN/GaN single quantum well structures grown with and without InGaN underlayers. *Journal of Alloys and Compounds*, **2020**, 845, 156269	5.6	2
2051	In Situ Observation of □Ga2O3 Schottky Diode Failure Under Forward Biasing Condition. *IEEE Transactions on Electron Devices*, **2020**, 67, 3056-3061	2.7	5
2050	Proton Irradiation of High Aluminum Content AlGaN Polarization Doped Field Effect Transistors. *ECS Journal of Solid State Science and Technology*, **2020**, 9, 025003	1.9	2
2049	Plasma etching of wide bandgap and ultrawide bandgap semiconductors. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2020**, 38, 020802	2.7	12
2048	Pulsed fast reactor neutron irradiation effects in Si doped n-type □Ga2O3. *Journal Physics D: Applied Physics*, **2020**, 53, 274001	2.9	10
2047	Electric field dependence of major electron trap emission in bulk □Ga2O3: Poole□renkel effect versus phonon-assisted tunneling. *Journal Physics D: Applied Physics*, **2020**, 53, 304001	2.9	7
2046	Editors□Choice□lectrical Properties and Deep Traps in □Ga2O3:Sn Films Grown on Sapphire by Halide Vapor Phase Epitaxy. *ECS Journal of Solid State Science and Technology*, **2020**, 9, 045003	1.9	11
2045	Nanosensor networks for health-care applications **2020**, 405-417		2
2044	Determination of dielectric axes and transition moment directions in □Ga2O3 from the polarization dependence of vibrational spectra. *Journal of Applied Physics*, **2020**, 127, 055702	2.4	8
2043	High temperature operation to 500 °C of AlGaN graded polarization-doped field-effect transistors. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2020**, 38, 033202	1.2	
2042	Role of hole trapping by deep acceptors in electron-beam-induced current measurements in □Ga2O3 vertical rectifiers. *Journal Physics D: Applied Physics*, **2020**, 53, 495108	2.9	9
2041	Neutron Irradiation of AlGaN Polarization Doped Field Effect Transistors. *ECS Journal of Solid State Science and Technology*, **2020**, 9, 065007	1.9	1
2040	Editors□Choice□ibrational Properties of Oxygen-Hydrogen Centers in H+- and D+-Implanted Ga2O3. *ECS Journal of Solid State Science and Technology*, **2020**, 9, 125006	1.9	5
2039	Preface□SS Focus Issue on Gallium Oxide Based Materials and Devices II. *ECS Journal of Solid State Science and Technology*, **2020**, 9, 060001	1.9	0
2038	Design and implementation of floating field ring edge termination on vertical geometry □Ga2O3 rectifiers. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2020**, 38, 063414	2.7	1

2037	Diodes 1. *Springer Series in Materials Science*, **2020**, 661-688	0.9	
2036	Opportunities and Challenges in MOCVD of Ga2O3 for Power Electronic Devices. *Selected Topics in Electornics and Systems*, **2020**, 127-144	0	
2035	A Reconfigurable, Pulse-shaping Potentiometric Readout System for Bio-Sensing Transistors. *Annual International Conference of the IEEE Engineering in Medicine and Biology Society IEEE Engineering in Medicine and Biology Society Annual International Conference*, **2019**, 2019, 5761-5764	0.8	2
2034	Effects of Hydrogen Plasma Treatment Condition on Electrical Properties of Ga2O3. *ECS Journal of Solid State Science and Technology*, **2019**, 8, P661-P666	1.9	4
2033	Forward bias degradation and thermal simulations of vertical geometry Ga2O3 Schottky rectifiers. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2019**, 37, 061205	1.2	8
2032	Band Offsets of Insulating & Semiconducting Oxides on (AlxGa1-x)O3. *ECS Transactions*, **2019**, 92, 79-88	0.5	5
2031	Diffusion of implanted Ge and Sn in Ga2O3. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2019**, 37, 051204	1.2	14
2030	Effects of InAlN underlayer on deep traps detected in near-UV InGaN/GaN single quantum well light-emitting diodes. *Journal of Applied Physics*, **2019**, 126, 125708	2.4	14
2029	Effect of thermal annealing for W/Ga2O3 Schottky diodes up to 600 °C. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2019**, 37, 061201	1.2	8
2028	Radiation damage effects in Ga2O3 materials and devices. *Journal of Materials Chemistry C*, **2019**, 7, 10-24	7	76
2027	Electron injection-induced effects in Si-doped Ga2O3. *AIP Advances*, **2019**, 9, 015127	1.5	10
2026	Electrical Properties, Deep Trap and Luminescence Spectra in Semi-Insulating, Czochralski Ga2O3 (Mg). *ECS Journal of Solid State Science and Technology*, **2019**, 8, Q3019-Q3023	1.9	23
2025	Device processing and junction formation needs for ultra-high power Ga2O3 electronics. *MRS Communications*, **2019**, 9, 77-87	2.7	11
2024	Switching Behavior and Forward Bias Degradation of 700V, 0.2A, Ga2O3Vertical Geometry Rectifiers. *ECS Journal of Solid State Science and Technology*, **2019**, 8, Q3028-Q3033	1.9	11
2023	Implementation of a 900V Switching Circuit for High Breakdown Voltage Ga2O3 Schottky Diodes. *ECS Journal of Solid State Science and Technology*, **2019**, 8, Q3229-Q3234	1.9	5
2022	Fast Cerebrospinal Fluid Detection Using Inexpensive Modular Packaging with Disposable Testing Strips. *Journal of the Electrochemical Society*, **2019**, 166, B708-B712	3.8	4
2021	Vertical geometry 33.2 A, 4.8 MW cm2 Ga2O3 field-plated Schottky rectifier arrays. *Applied Physics Letters*, **2019**, 114, 232106	3.3	22
2020	Defects at the surface of Ga2O3 produced by Ar plasma exposure. *APL Materials*, **2019**, 7, 061102	5.6	24

2019	Will surface effects dominate in quasi-two-dimensional gallium oxide for electronic and photonic devices?. *Nanoscale Horizons*, **2019**, 4, 1251-1255	10.6	6
2018	Deep trap analysis in green light emitting diodes: Problems and solutions. *Journal of Applied Physics* , **2019**, 125, 215701	2.4	4
2017	Comparison of Dual-Stack Dielectric Field Plates on Ga2O3 Schottky Rectifiers. *ECS Journal of Solid State Science and Technology*, **2019**, 8, Q3221-Q3225	1.9	12
2016	Thermoreflectance Temperature Mapping of Ga2O3 Schottky Barrier Diodes. *ECS Transactions*, **2019**, 89, 3-7	0.5	3
2015	Deep trap spectra of Sn-doped Ga2O3 grown by halide vapor phase epitaxy on sapphire. *APL Materials*, **2019**, 7, 051103	5.6	17
2014	Operation Up to 500 C of Al0.85Ga0.15N/Al0.7Ga0.3N High Electron Mobility Transistors. *IEEE Journal of the Electron Devices Society*, **2019**, 7, 444-452	1.9	23
2013	Electrical Properties, Deep Levels and Luminescence Related to Fe in Bulk Semi-Insulating Ga2O3 Doped with Fe. *ECS Journal of Solid State Science and Technology*, **2019**, 8, Q3091-Q3096	1.9	17
2012	Editors' ChoiceHydrogen Centers in Ga2O3: Infrared Spectroscopy and Density Functional Theory. *ECS Journal of Solid State Science and Technology*, **2019**, 8, Q3103-Q3110	1.9	39
2011	Damage Recovery and Dopant Diffusion in Si and Sn Ion Implanted Ga2O3. *ECS Journal of Solid State Science and Technology*, **2019**, 8, Q3133-Q3139	1.9	16
2010	Reverse Breakdown in Large Area, Field-Plated, Vertical Ga2O3Rectifiers. *ECS Journal of Solid State Science and Technology*, **2019**, 8, Q3159-Q3164	1.9	12
2009	Deep traps and persistent photocapacitance in (Al0.14 Ga0.86)2O3/Ga2O3 heterojunctions. *Journal of Applied Physics*, **2019**, 125, 095702	2.4	1
2008	Heterojunction Bipolar Transistor: 2D Material-Based Vertical Double Heterojunction Bipolar Transistors with High Current Amplification (Adv. Electron. Mater. 3/2019). *Advanced Electronic Materials*, **2019**, 5, 1970015	6	0
2007	Valence band offsets for ALD SiO2 and Al2O3 on (InxGa1)2O3 for x = 0.250.74. *APL Materials*, **2019**, 7, 071115	5.6	9
2006	The role of annealing ambient on diffusion of implanted Si in Ga2O3. *AIP Advances*, **2019**, 9, 085111	1.5	15
2005	Extreme Temperature Operation of Ultra-Wide Bandgap AlGaN High Electron Mobility Transistors. *IEEE Transactions on Semiconductor Manufacturing*, **2019**, 32, 473-477	2.3	9
2004	Hydrogen plasma treatment of Ga2O3: Changes in electrical properties and deep trap spectra. *Applied Physics Letters*, **2019**, 115, 032101	3.3	29
2003	Band Alignment of Atomic Layer Deposited SiO2 and Al2O3 on (AlxGa1-x)2O3 for x = 0.2-0.65. *ECS Journal of Solid State Science and Technology*, **2019**, 8, P351-P356	1.9	8
2002	Valence and Conduction Band Offsets for InN and III-Nitride Ternary Alloys on (201) Bulk Ga2O3. *ECS Journal of Solid State Science and Technology*, **2019**, 8, Q3154-Q3158	1.9	9

2001	Thermal Simulations of High Current Ga2O3 Schottky Rectifiers. *ECS Journal of Solid State Science and Technology*, **2019**, 8, Q3195-Q3201	1.9	14
2000	60Co Gamma Ray Damage in Homoepitaxial Ga2O3Schottky Rectifiers. *ECS Journal of Solid State Science and Technology*, **2019**, 8, Q3041-Q3045	1.9	9
1999	Valence- and Conduction-Band Offsets for Atomic-Layer-Deposited Al2O3 on (010) (Al0.14Ga0.86)2O3. *Journal of Electronic Materials*, **2019**, 48, 1568-1573	1.9	18
1998	III-Nitride Nanowires as Building Blocks for Advanced Light Emitting Diodes. *Physica Status Solidi (B): Basic Research*, **2019**, 256, 1800589	1.3	4
1997	Impact of Electron Injection and Temperature on Minority Carrier Transport in Alpha-Irradiated Ga2O3 Schottky Rectifiers. *ECS Journal of Solid State Science and Technology*, **2019**, 8, Q3050-Q3053	1.9	7
1996	Effect of Annealing on the Band Alignment of ALD SiO2 on (AlxGa1-x)2O3 for x = 0.2 - 0.65. *ECS Journal of Solid State Science and Technology*, **2019**, 8, P751-P756	1.9	4
1995	(Invited) Comparison of High Voltage, Vertical Geometry Ga2O3 Rectifiers with GaN and SiC. *ECS Transactions*, **2019**, 92, 15-24	0.5	1
1994	Annealing of Proton and Alpha Particle Damage in Au-W/Ga2O3 Rectifiers. *ECS Journal of Solid State Science and Technology*, **2019**, 8, P799-P804	1.9	1
1993	Opportunities and Challenges in MOCVD of Ga2O3 for Power Electronic Devices. *International Journal of High Speed Electronics and Systems*, **2019**, 28, 1940007	0.5	3
1992	Optimization of Edge Termination Techniques for Ga2O3 Schottky Rectifiers. *ECS Journal of Solid State Science and Technology*, **2019**, 8, Q234-Q239	1.9	6
1991	Temperature-Dependent Electrical Characteristics of Ga2O3Diodes with W Schottky Contacts up to 500C. *ECS Journal of Solid State Science and Technology*, **2019**, 8, Q3007-Q3012	1.9	23
1990	Valence and conduction band offsets for sputtered AZO and ITO on (010) (Al0.14Ga0.86)2O3. *Semiconductor Science and Technology*, **2019**, 34, 025006	1.7	6
1989	2D Material-Based Vertical Double Heterojunction Bipolar Transistors with High Current Amplification. *Advanced Electronic Materials*, **2019**, 5, 1800745	6	14
1988	Defect States Determining Dynamic Trapping-Detrapping in Ga2O3 Field-Effect Transistors. *ECS Journal of Solid State Science and Technology*, **2019**, 8, Q3013-Q3018	1.9	18
1987	Dynamic Switching Characteristics of 1 A Forward Current $boldsymbol{beta}$ -Ga2O3 Rectifiers. *IEEE Journal of the Electron Devices Society*, **2019**, 7, 57-61	1.9	18
1986	Effect of Deposition Method on Valence Band Offsets of SiO2 and Al2O3 on (Al0.14Ga0.86)2O3. *ECS Journal of Solid State Science and Technology*, **2019**, 8, Q3001-Q3006	1.9	7
1985	Hydrogen in Ga2O3 **2019**, 191-210		5
1984	Dry etching of Ga2O3 **2019**, 263-285		2

1983	Band alignments of dielectrics on (201) Ga2O3 **2019**, 287-311		2
1982	Radiation damage in Ga2O3 **2019**, 313-328		3
1981	Two-Dimensionally Layered p-Black Phosphorus/n-MoS/p-Black Phosphorus Heterojunctions. *ACS Applied Materials & Interfaces*, **2018**, 10, 10347-10352	9.4	27
1980	Moisture Insensitive PMMA Coated Pt-AlGaN/GaN Diode Hydrogen Sensor and Its Thermal Stability. *ECS Journal of Solid State Science and Technology*, **2018**, 7, Q3009-Q3013	1.9	7
1979	Trapping Phenomena in InAlN/GaN High Electron Mobility Transistors. *ECS Journal of Solid State Science and Technology*, **2018**, 7, Q1-Q7	1.9	8
1978	Point defect induced degradation of electrical properties of Ga2O3 by 10 MeV proton damage. *Applied Physics Letters*, **2018**, 112, 032107	3.3	69
1977	A review of Ga2O3 materials, processing, and devices. *Applied Physics Reviews*, **2018**, 5, 011301	16.9	1011
1976	10 MeV proton damage in Ga2O3 Schottky rectifiers. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2018**, 36, 011206	1.2	23
1975	Effects of fluorine incorporation into Ga2O3. *Journal of Applied Physics*, **2018**, 123, 165706	2.4	17
1974	Effect of 1.5 MeV electron irradiation on Ga2O3 carrier lifetime and diffusion length. *Applied Physics Letters*, **2018**, 112, 082104	3.3	32
1973	Compensation and persistent photocapacitance in homoepitaxial Sn-doped Ga2O3. *Journal of Applied Physics*, **2018**, 123, 115702	2.4	57
1972	AlGaN/GaN Heterostructure Based Schottky Diode Sensors with ZnO Nanorods for Environmental Ammonia Monitoring Applications. *ECS Journal of Solid State Science and Technology*, **2018**, 7, Q3020-Q3024	1.9	13
1971	A comparative study of wet etching and contacts on (201) and (010) oriented Ga2O3. *Journal of Alloys and Compounds*, **2018**, 731, 118-125	5.6	35
1970	Hydrogen Sensing Characteristics of Pt Schottky Diodes on () and (010) Ga2O3Single Crystals. *ECS Journal of Solid State Science and Technology*, **2018**, 7, Q3180-Q3182	1.9	13
1969	Effect of alpha-particle irradiation dose on SiNx/AlGaN/GaN metalInsulator semiconductor high electron mobility transistors. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2018**, 36, 041203	1.2	4
1968	Zika virus detection using antibody-immobilized disposable cover glass and AlGaN/GaN high electron mobility transistors. *Applied Physics Letters*, **2018**, 113, 032101	3.3	15
1967	Electrical Properties of Bulk, Non-Polar, Semi-Insulating M-GaN Grown by the Ammonothermal Method. *ECS Journal of Solid State Science and Technology*, **2018**, 7, P260-P265	1.9	11
1966	Diffusion length of non-equilibrium minority charge carriers in Ga2O3 measured by electron beam induced current. *Journal of Applied Physics*, **2018**, 123, 185704	2.4	36

1965	Eighteen mega-electron-volt alpha-particle damage in homoepitaxial Ga2O3 Schottky rectifiers. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2018**, 36, 031205	1.2	13
1964	Ga2O3 Schottky rectifiers with 1 ampere forward current, 650 V reverse breakdown and 26.5 MW.cm-2 figure-of-merit. *AIP Advances*, **2018**, 8, 055026	1.5	46
1963	Structure and vibrational properties of the dominant O-H center in Ga2O3. *Applied Physics Letters* , **2018**, 112, 232104	3.3	57
1962	Defect States Induced in GaN-Based Green Light Emitting Diodes by Electron Irradiation. *ECS Journal of Solid State Science and Technology*, **2018**, 7, P323-P328	1.9	9
1961	Vertical Geometry, 2-A Forward Current Ga2O3 Schottky Rectifiers on Bulk Ga2O3 Substrates. *IEEE Transactions on Electron Devices*, **2018**, 65, 2790-2796	2.7	28
1960	Recombination properties of dislocations in GaN. *Journal of Applied Physics*, **2018**, 123, 161543	2.4	21
1959	Electrical properties, structural properties, and deep trap spectra of thin Ga2O3 films grown by halide vapor phase epitaxy on basal plane sapphire substrates. *APL Materials*, **2018**, 6, 121110	5.6	26
1958	Perspective: Ga2O3 for ultra-high power rectifiers and MOSFETS. *Journal of Applied Physics*, **2018**, 124, 220901	2.4	224
1957	Band alignment of atomic layer deposited SiO2 on (010) (Al0.14Ga0.86)2O3. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2018**, 36, 061207	1.2	13
1956	Band Offsets for Atomic Layer Deposited HfSiO4 on (Al0.14Ga0.86)2O3. *ECS Journal of Solid State Science and Technology*, **2018**, 7, P519-P523	1.9	8
1955	Effect of surface treatments on electrical properties of Ga2O3. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2018**, 36, 061201	1.2	30
1954	Electrical properties of bulk semi-insulating Ga2O3 (Fe). *Applied Physics Letters*, **2018**, 113, 142102	3.3	55
1953	Valence band offsets for CuI on (-201) bulk Ga2O3 and epitaxial (010) (Al0.14Ga0.86)2O3. *Applied Physics Letters*, **2018**, 113, 182101	3.3	12
1952	Hole traps and persistent photocapacitance in proton irradiated Ga2O3 films doped with Si. *APL Materials*, **2018**, 6, 096102	5.6	47
1951	Effect of proton irradiation energy on SiNx/AlGaN/GaN metal-insulator semiconductor high electron mobility transistors. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2018**, 36, 052202	1.2	10
1950	Defects responsible for charge carrier removal and correlation with deep level introduction in irradiated Ga2O3. *Applied Physics Letters*, **2018**, 113, 092102	3.3	42
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